



P3M12080K3 SiC MOS N-Channel Enhancement Mode

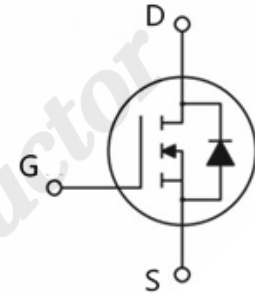
V_{RRM}	= 1200	V
I_D	= 47	A
$I_D (100^\circ\text{C})$	= 33	A
$R_{DS(on)}$	= 80	m Ω

SiC MOS P3M12080K3 N-Channel Enhancement Mode



Features

- Qualified to AEC-Q101
- High Blocking Voltage with Low On-Resistance
- High-Frequency Operation
- Ultra-Small Q_{gd}
- 100% UIS tested



Standards Benefits

- Improve System Efficiency
- Increase Power Density
- Reduce Heat Sink Requirements
- Reduction of System Cost

TO-247-3

Gate	1
Drain	2
Source	3

Application

- Solar Inverters
- EV Battery Chargers
- High Voltage DC/DC Converters
- Switch Mode Power Supplies



Order Information

Part number	Package	Marking
P3M12080K3	TO-247-3	P3M12080K3



Contents

Features	1
Standards Benefits	1
Application	1
Order Information.....	1
Contents	2
1. Maximum Ratings	3
2. Electrical Characteristics.....	4
3. Reverse Diode Characteristics.....	5
4. Thermal Characteristics	6
5. Typical Performance	6
6. Package Outlines.....	11

PN Junction Semiconductor



1. Maximum Ratings

At $T_J = 25^\circ\text{C}$, unless specified otherwise

Parameter	Symbol	Value	Unit	Test Conditions
Drain - Source Voltage	V_{DSmax}	1200	V	$V_{GS} = -3\text{V}$ $I_D = 100\mu\text{A}$
Gate - Source Voltage (dynamic)	V_{GSmax}	-8 / +19	V	AC ($f > 1\text{Hz}$)
Gate - Source Voltage (static)	V_{GSop}	-3 / +15	V	Static
Continuous Drain Current	I_D	47	A	$V_{GS} = 15\text{V}$ $T_C = 25^\circ\text{C}$
		33		$V_{GS} = 15\text{V}$ $T_C = 100^\circ\text{C}$
Power Dissipation	P_D	221	W	
Operating Junction	T_J	-55 To +175	$^\circ\text{C}$	
Storage Temperature	T_{stg}	-55 To +175	$^\circ\text{C}$	
Solder Temperature	T_L	260	$^\circ\text{C}$	
Mounting Torque	M_d	1 8.8	Nm lbf-in	M3 or 6-32 screw



2. Electrical Characteristics

At $T_J = 25^\circ\text{C}$, unless specified otherwise

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	1200	/	/	V	$V_{GS} = -3V$ $I_D = 100\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	1.8	2.2	/	V	$V_{DS} = V_{GS}$ $I_D = 30mA$
		/	1.45	/	V	$V_{DS} = V_{GS}$ $I_D = 30mA$ $T_J = 175^\circ\text{C}$
Drain Current	I_{DSS}	/	0.14	10	μA	$V_{GS} = -3V$ $V_{DS} = 1200V$
Gate-Source Leakage Current	I_{GSS}	/	20	250	nA	$V_{GS} = 15V$ $V_{DS} = 0V$
Drain-Source On-State Resistance	$R_{DS(on)}$	/	80	96	m Ω	$V_{GS} = 15V$ $I_D = 20A$
Transconductance	g_{fs}	/	10.65	/	S	$V_{DS} = 20V$ $I_{DS} = 20A$
		/	11.5	/	S	$V_{DS} = 20V$ $I_{DS} = 20A$ $T_J = 175^\circ\text{C}$
Input Capacitance	C_{iss}	/	2070	/	pF	$V_{GS} = 0V$ $V_{DS} = 800V$ $f = 1MHz$ $V_{AC} = 25mV$
Output Capacitance	C_{oss}	/	78	/	pF	
Reverse Transfer Capacitance	C_{rss}	/	8	/	pF	
Coss Stored Energy	E_{oss}	/	53.1	/	μJ	
Turn-on Energy	E_{on}	/	470	/	μJ	
Turn-off Energy	E_{off}	/	31	/		$I_D = 20A$ $R_G = 1\Omega$



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Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Turn-On Delay Time	$t_{d(on)}$	/	15.68	/	ns	$V_{DS} = 800V$ $V_{GS} = -3/15V$ $I_D = 20A$ $R_G = 1\Omega$
Rise Time	t_r	/	29.12	/		
Turn-Off Delay Time	$t_{d(off)}$	/	24.64	/		
Fall Time	t_f	/	17.6	/		
Internal Gate Resistance	$R_{G(int)}$	/	1.76	/	Ω	$f = 1MHz$ $V_{AC} = 25mV$
Gate to Source Charge	Q_{gs}	/	20.8	/	nC	$V_{DS} = 800V$ $I_{DS} = 20A$ $V_{GS} = -3 \text{ to } 15V$ $I_G = 20mA$
Gate to Drain Charge	Q_{gd}	/	13.5	/		
Total Gate Charge	Q_g	/	57.2	/		

3. Reverse Diode Characteristics

At $T_J = 25^\circ C$, unless specified otherwise

Parameter	Symbol	Value		Unit	Test Conditions
		Typ.	Max.		
Diode Forward Voltage	V_{SD}	4.8	/	V	$V_{GS} = -3V$ $I_{SD} = 10A$
		4.6	/	V	$V_{GS} = -3V$ $I_{SD} = 10A$ $T_J = 175^\circ C$
Continuous Diode Forward Current	I_S	32	/	A	$V_{GS} = -3V$
Reverse Recover Time	t_{rr}	33.44	/	ns	$V_{GS} = -3V$ $I_{SD} = 20A$ $V_R = 800V$ $dI_f/dt = 4000A/\mu s$ $T_J = 25^\circ C$
Reverse Recovery Charge	Q_{rr}	520.14	/	nC	
Peak Reverse Recovery Current	I_{rrm}	22.26	/	A	

4. Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.68	$^{\circ}C/W$

5. Typical Performance

At $T_J = 25^{\circ}C$, unless specified otherwise

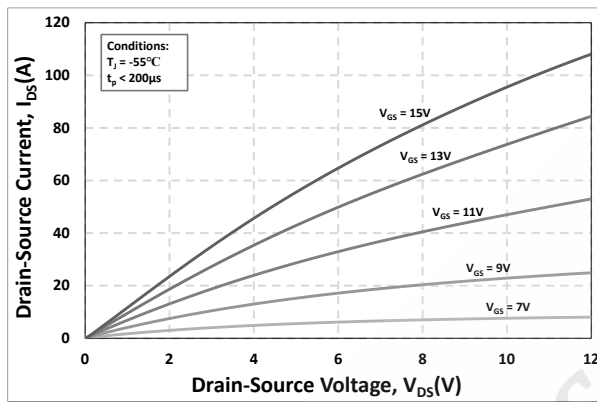


Figure 1. Output Characteristics $T_J = -55^{\circ}C$

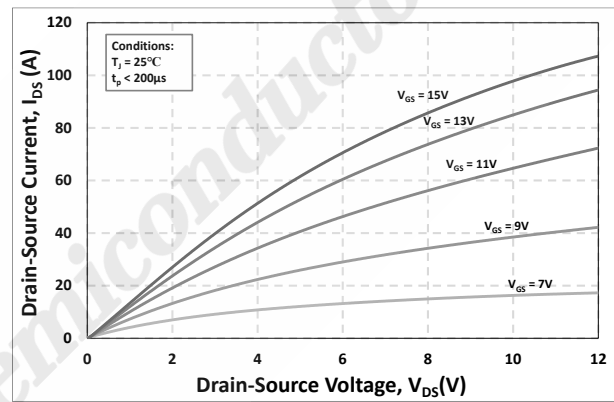


Figure 2. Output Characteristics $T_J = 25^{\circ}C$

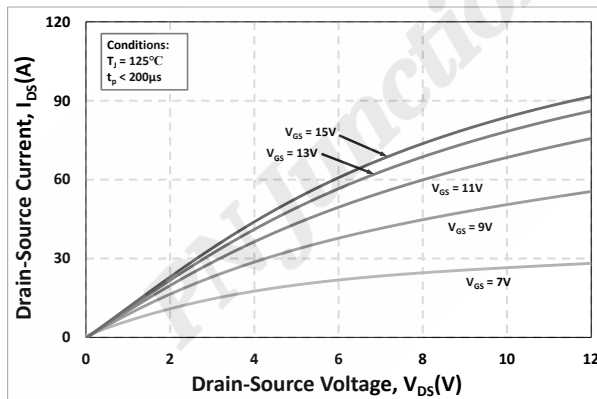


Figure 3. Output Characteristics $T_J = 125^{\circ}C$

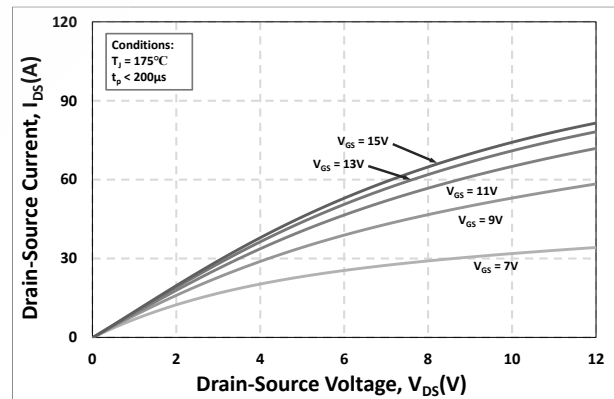


Figure 4. Output Characteristics $T_J = 175^{\circ}C$

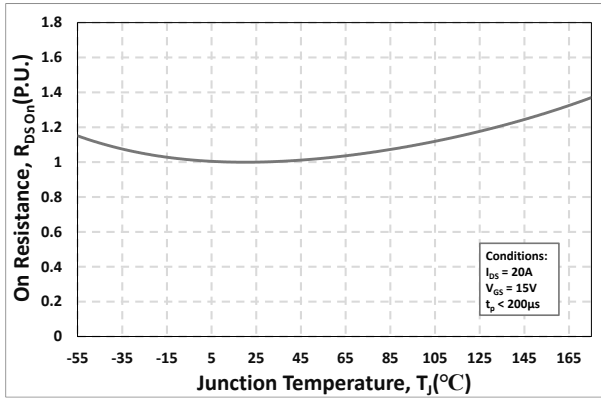


Figure 5. Normalized On-Resistance vs. Temperature

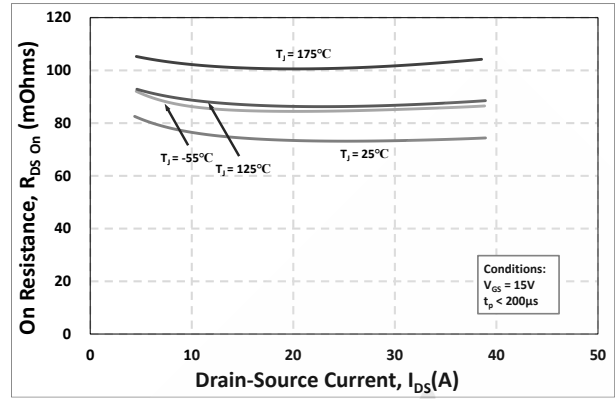


Figure 6. On-Resistance vs. Drain Current Various Temperatures

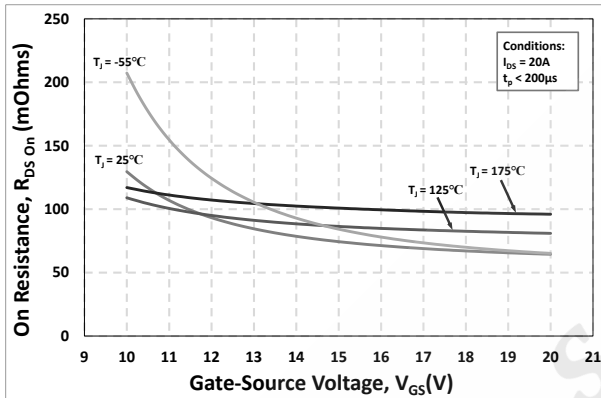


Figure 7. On-Resistance vs. Gate-Source Voltage

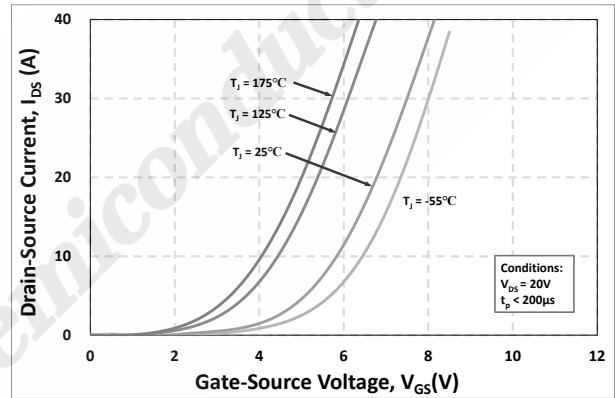


Figure 8. Transfer Characteristic for Various Junction Temperatures

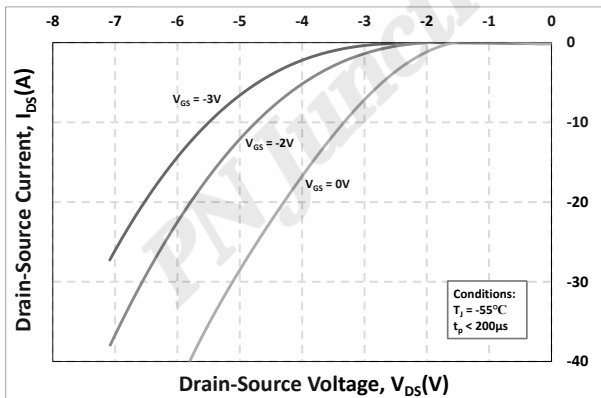


Figure 9. Body Diode Characteristic at -55°C

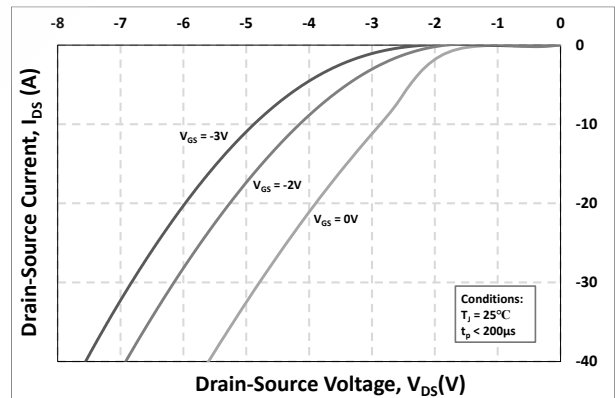


Figure 10. Body Diode Characteristic at 25°C

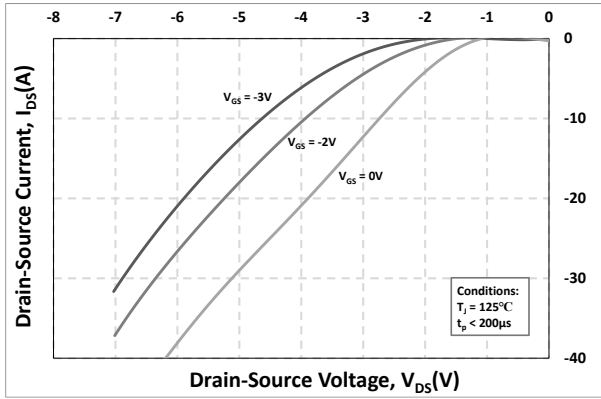


Figure 11. Body Diode Characteristic at 125°C

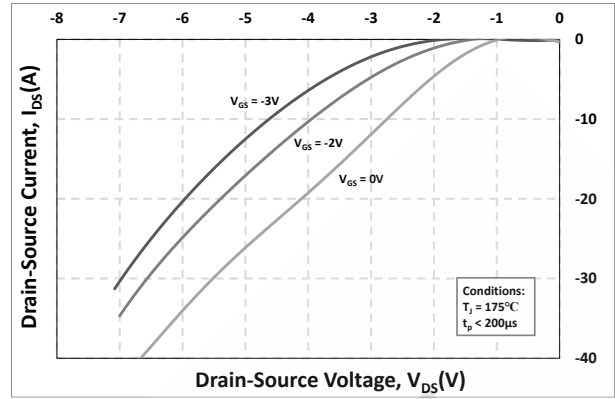


Figure 12. Body Diode Characteristic at 175°C

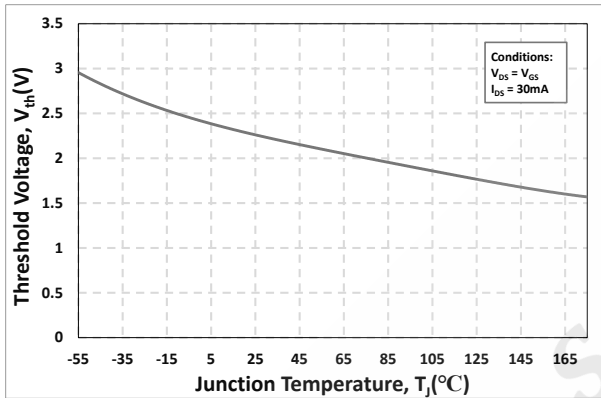


Figure 13. Threshold Voltage vs. Temperature

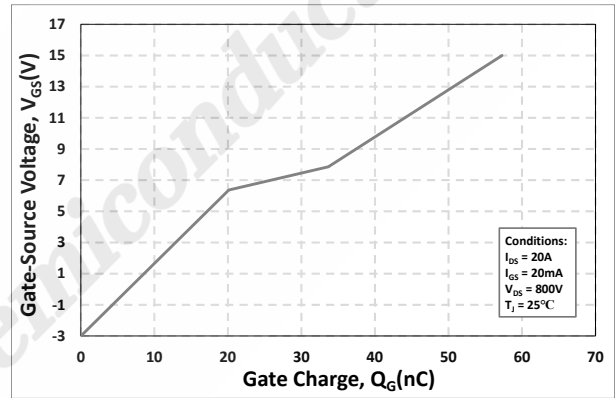


Figure 14. Gate Charge Characteristics

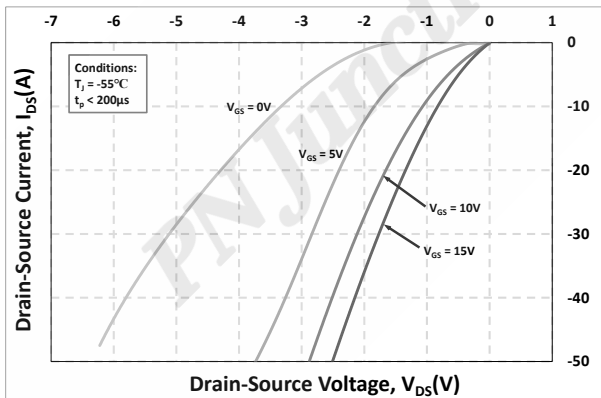


Figure 15. 3rd Quadrant Characteristic at -55°C

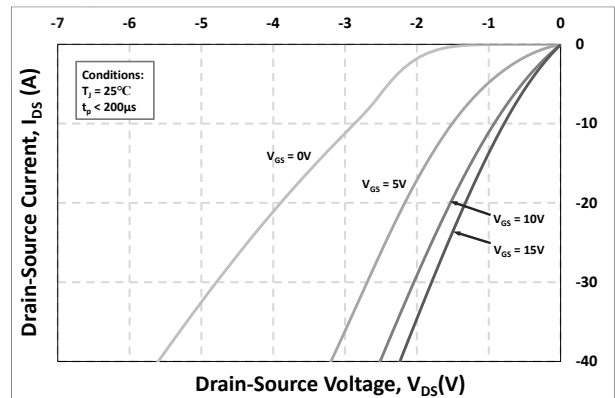


Figure 16. 3rd Quadrant Characteristic at 25°C

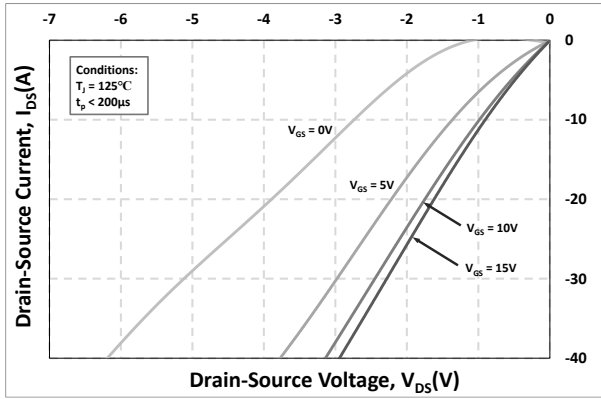


Figure 17. 3rd Quadrant Characteristic at 125°C

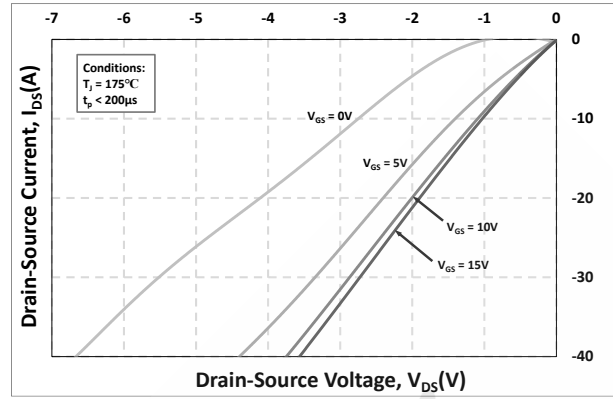


Figure 18. 3rd Quadrant Characteristic at 175°C

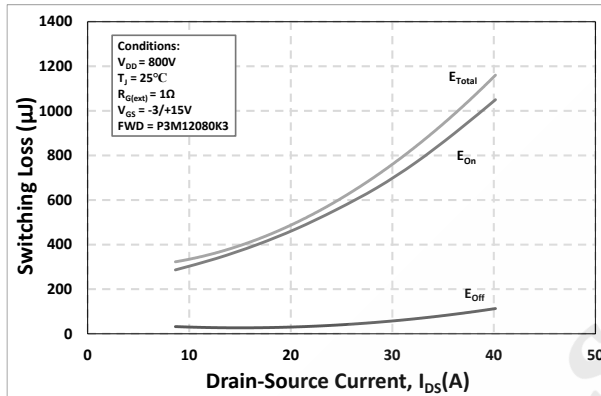


Figure 19. Clamped Inductive Switching Energy vs. Drain Current (V_{DD}= 400V)

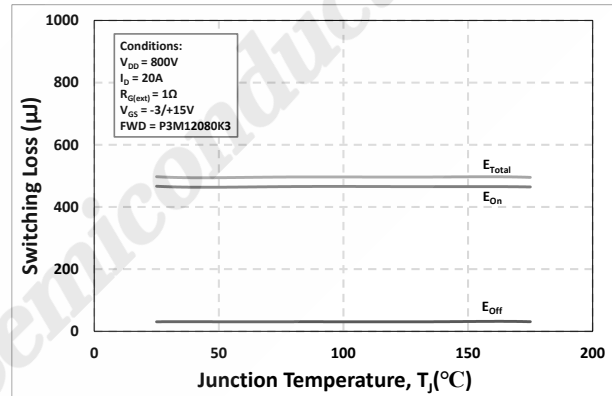


Figure 20. Clamped Inductive Switching Energy vs. R_G(ext)

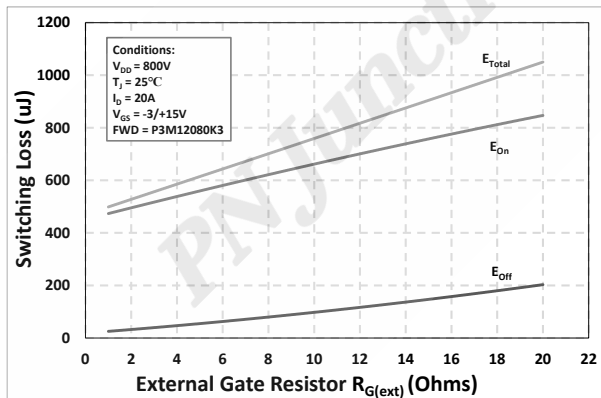


Figure 21. Clamped Inductive Switching Energy vs. Temperature

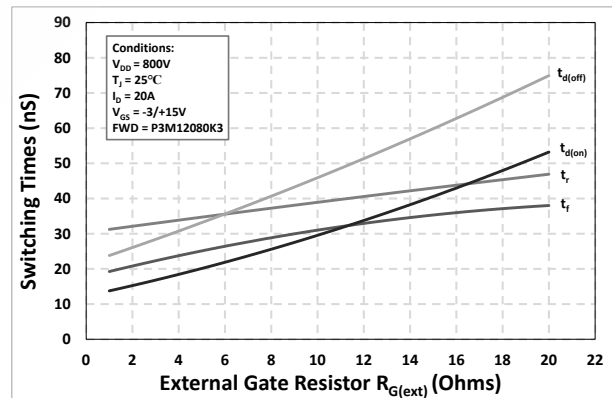


Figure 22. Switching Times vs. R_G(ext)

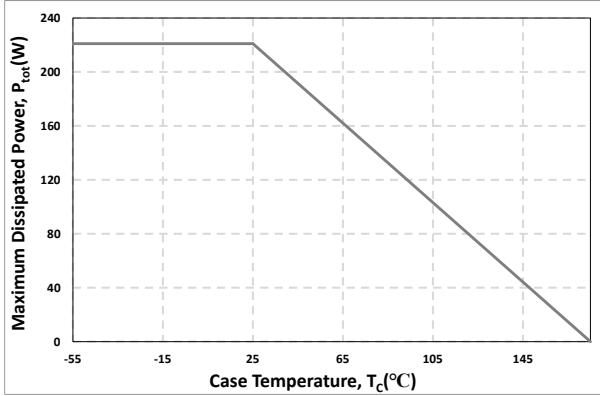


Figure 23. Maximum Power Dissipation Derating vs. Case Temperature

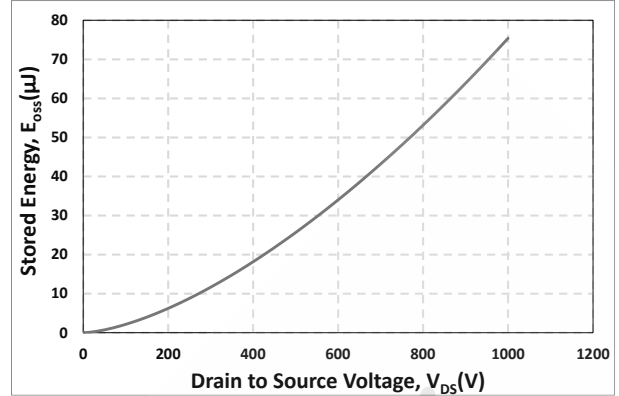


Figure 24. Output Capacitor Stored Energy

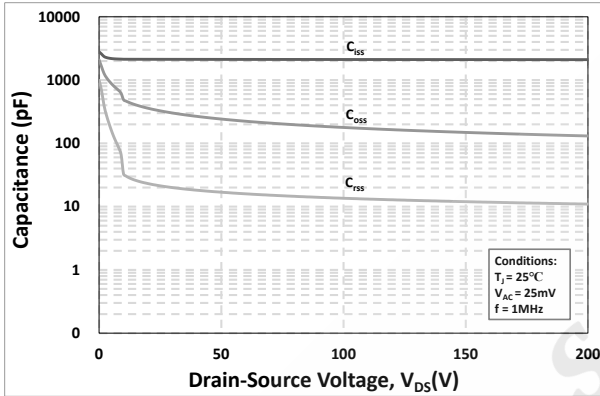


Figure 25. Capacitances vs. Drain-Source Voltage (0 - 200V)

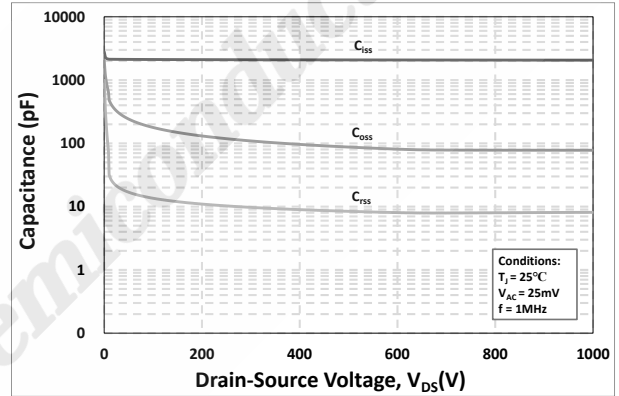


Figure 26. Capacitances vs. Drain-Source Voltage (0 - 1000V)

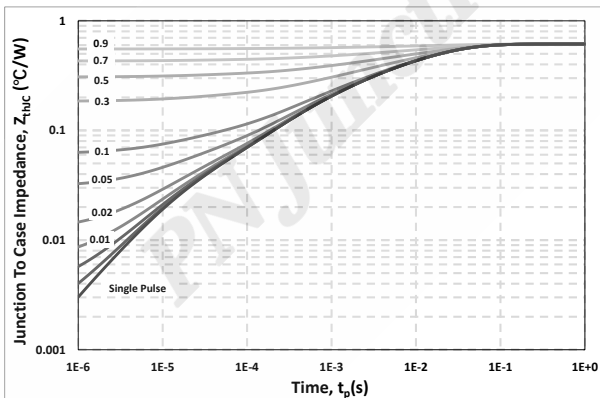


Figure 27. Transient Thermal Impedance (Junction - Case)

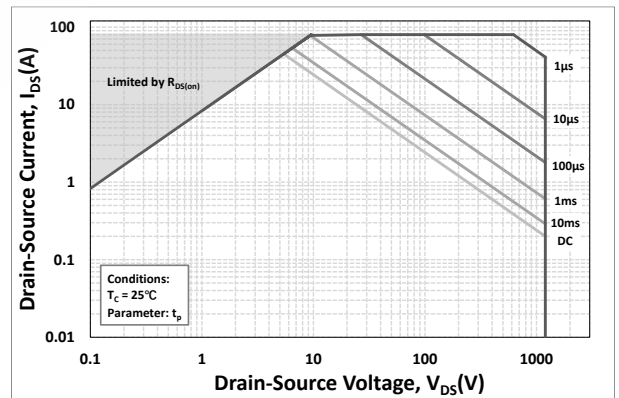
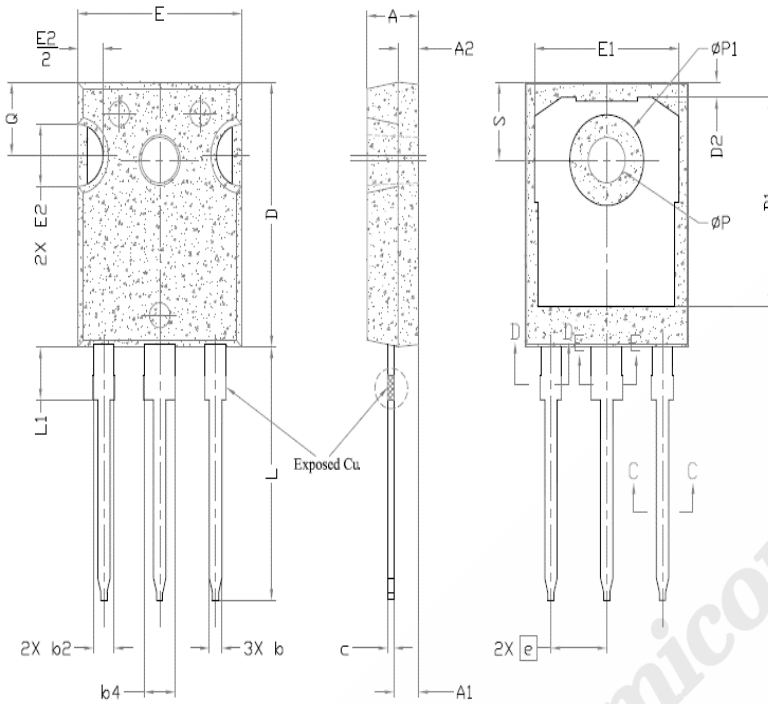


Figure 28. Safe Operating Area

6. Package Outlines



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.50	2.00	2.49	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
c	0.55	0.60	0.69	6
c1	0.55	0.60	0.65	
D	20.80	20.95	21.10	4
D1	16.25	16.55	17.65	5
D2	0.51	1.19	1.35	
E	15.75	15.94	16.13	4
E1	13.46	14.02	14.16	5
E2	4.32	4.91	5.49	3
e	5.44BSC			
L	19.81	20.07	20.32	
L1	4.10	4.19	4.40	6
ØP	3.56	3.61	3.65	7
ØP1	7.19REF.			
Q	5.39	5.79	6.20	
S	6.04	6.17	6.30	

Drawing and dimensions

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